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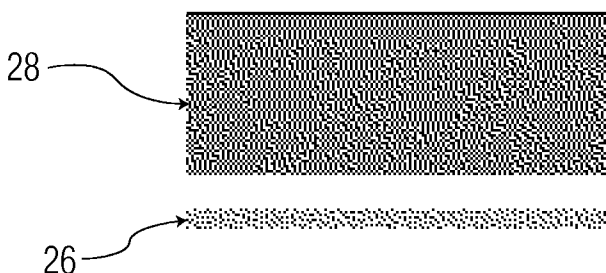
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(54) Title: DOPING PROFILE IMPROVEMENT OF IN-SITU DOPED N-TYPE EMITTERS



(57) Abstract: A method for forming an emitter-base junction. The method includes the steps of: providing a base layer (26); and growing a doped mono-emitter layer (28) on the base layer (26) using a gas flow comprised of a set of process gases, wherein gas flow includes an addition of a germanium (Ge) source to the process gases for the first few seconds of the gas flow.

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